
Module Leader
Prof F Udrea

Lecturer
Prof F Udrea

Timing and Structure
Michaelmas term. 14 lectures (includes one example class). Assessment: 100% exam. Note: First two lectures are ONLINE. check timetable in Moodle.

Prerequisites
3B3 & 3B5 useful

Aims
The aims of the course are to:

- provide an introduction to the world of modern power semiconductor devices, and their applications in the electronics Industry.
- cover material specific to power semiconductor devices not covered in other modules in semiconductors.

Objectives
As specific objectives, by the end of the course students should be able to:

- understand how the design of power semiconductor devices takes account of high voltage and currents
- explain the practical operating conditions pertaining to power semiconductor devices
- analyse power circuit segments
- know the features of the main types of power electronic devices
- understand the semiconductor technologies in power devices

Content
Introduction
Introduction to power electronics and power devices. Basics of power electronics, power devices and applications. P-N junction theory.

Power Diodes
High voltage pn junction theory. Breakdown theory. None punch-through (NPT) and punch-through (PT) high voltage junction. On-state - high level injection. Lifetime. Turn-off reverse recovery
Field Control
Curvature effects in high voltage junctions, Edge effects, Field plates, Terminations in power devices.

Power Bipolar Devices
Bipolar Juction transistor (BJT).

Thyristsors
The thyristor (concept & technology). The GTO thyristor, Switching aids for transistors and thyristors.

Power MOS Devices
The power MOSFET: Concept, modes of operation. trade-offs.

Power MOSFET Modelling
The power MOSFET modelling, technologies and advanced devices.

Insulted Gate Bipolar Transistors
The Insulted Gate Bipolar Transistor (IGBT): modes of operation. trade-offs.

IGBTs II
The IGBTs, modelling, technologies and advanced concepts.

Power Integrated Circuits (PICs)
Power Intergated Circuits (PICS) and High Voltage Integrated Circuits (HVICs): introduction, lateral devices for PICs and HVICs, concepts, modes of operation.

Wide bandgap materials and devices.
Figure of merit (FOM) for wide bandgap materials. Architectures, designs and challenges of Silicon Carbide (SiC) and Gaslium Nitride (GaN) devices.

Coursework
n/a

Booklists
Please refer to the Booklist for Part IIB Courses for references to this module, this can be found on the associated Moodle course.

Examination Guidelines
Please refer to Form & conduct of the examinations [2].

UK-SPEC
The UK Standard for Professional Engineering Competence (UK-SPEC) [3] describes the requirements that have
to be met in order to become a Chartered Engineer, and gives examples of ways of doing this.

UK-SPEC is published by the Engineering Council on behalf of the UK engineering profession. The standard has been developed, and is regularly updated, by panels representing professional engineering institutions, employers and engineering educators. Of particular relevance here is the [Accreditation of Higher Education Programmes’ (AHEP) document](http://www.engc.org.uk/standards-guidance/standards/accreditation-of-higher-education-programmes-ahep/) which sets out the standard for degree accreditation.

The [Output Standards Matrices](http://teaching.eng.cam.ac.uk/content/output-standards-matrices) indicate where each of the Output Criteria as specified in the AHEP 3rd edition document is addressed within the Engineering and Manufacturing Engineering Triposes.

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Links
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